



DMT12H007LPS

120V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI5060-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	Ι _D T _C = +25°C
120V	7.8mΩ @ V _{GS} = 10V	90A
	14.1mΩ @ V_{GS} = 4.5V	70A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Switching
- **DC-DC** Converters

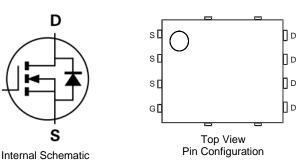
Features

- 100% Unclamped Inductive Switching (UIS) Test in Production -Ensures More Reliable and Robust End Application
- Thermally Efficient Package Cooler Running Applications
- High Conversion Efficiency
- Low RDS(ON) Minimizes On-State Losses
- <1.1mm Package Profile Ideal for Thin Applications
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts gualified to AEC-Q101, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.
- https://www.diodes.com/guality/product-definitions/

Mechanical Data

- Case: PowerDI[®]5060-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.097 grams (Approximate)





Ordering Information (Note 4)

	Part Number	Case	Packaging	
	DMT12H007LPS-13 PowerDI5060-8		2,500 / Tape & Reel	
Notes:	otes: 1 EU Directive 2002/95/EC (RoHS) 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant All applicable RoHS exemptions applied			

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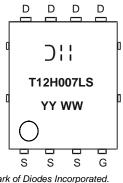
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

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3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



☐ Landracturer's Marking T12H007LS = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 19 = 2019) WW = Week Code (01 to 53)



Maximum Ratings ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage		V _{DSS}	120	V
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 6)	T _C = +25°C T _C = +70°C	ID	90 72	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	360	А
Continuous Body Diode Forward Current (Note 6)	T _C = +25°C	Is	80	А
Pulsed Body Diode Forward Current (Note 6)	T _C = +25°C	I _{SM}	360	А
Avalanche Current, L = 3mH		I _{AS}	15.6	А
Avalanche Energy, L = 3mH		E _{AS}	365	mJ

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Characteristic	Symbol	Тур	
Total Power Dissipation (Note 5)	PD	2.9	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	42	°C/W
Total Power Dissipation (Note 6)	PD	96	W
Thermal Resistance, Junction to Case (Note 6)	R _{0JC}	1.3	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	С°

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

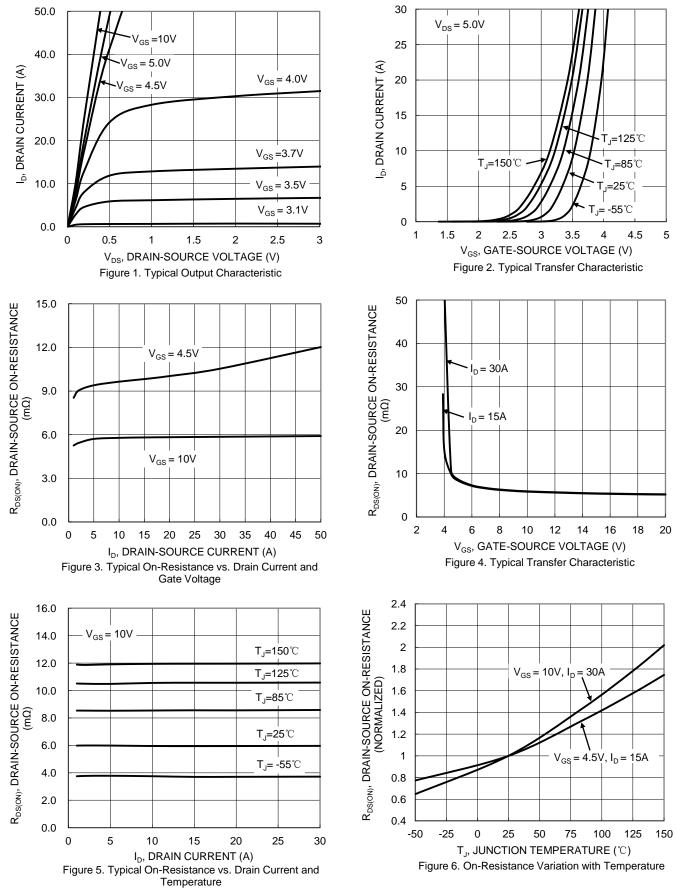
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				•	•	-	
Drain-Source Breakdown Voltage	BV _{DSS}	120	—	—	V	$V_{GS} = 0V, I_D = 10mA$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	1	μA	$V_{DS} = 96V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS		—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1.3	_	2.5	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	Proven	_	6	7.8	mΩ	$V_{GS} = 10V, I_D = 30A$	
	R _{DS(ON)}		10	14.1	11152	$V_{GS} = 4.5V, I_D = 15A$	
Diode Forward Voltage	V _{SD}		0.8	1.2	V	$V_{GS} = 0V, I_{S} = 30A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		3224	-		$V_{DS} = 60V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss		454	-	pF		
Reverse Transfer Capacitance	C _{rss}		17.8	-			
Gate Resistance	R _G	_	1.9	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	_	49	—			
Gate-Source Charge	Q _{gs}		11.6	—	nC	$V_{DS} = 60V, I_{D} = 25A$	
Gate-Drain Charge	Q _{gd}		11.4	-			
Turn-On Delay Time	t _{D(ON)}		7.9	—		$V_{DD} = 60V, V_{GS} = 10V,$ $I_D = 25A, R_G = 2.7\Omega$	
Turn-On Rise Time	t _R		15.4	-	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	30	—	115		
Turn-Off Fall Time	t _F		19.1	_			
Reverse Recovery Time	t _{RR}	_	54	_	ns	$I_{-} = 250$ di/dt = 1000/(up	
Reverse Recovery Charge	Q _{RR}	_	100	—	nC	$I_F = 25A, di/dt = 100A/\mu s$	

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
Thermal resistance from junction to soldering point (on the exposed drain pad).
Short duration pulse test used to minimize self-heating effect. Notes:

8. Guaranteed by design. Not subject to product testing.



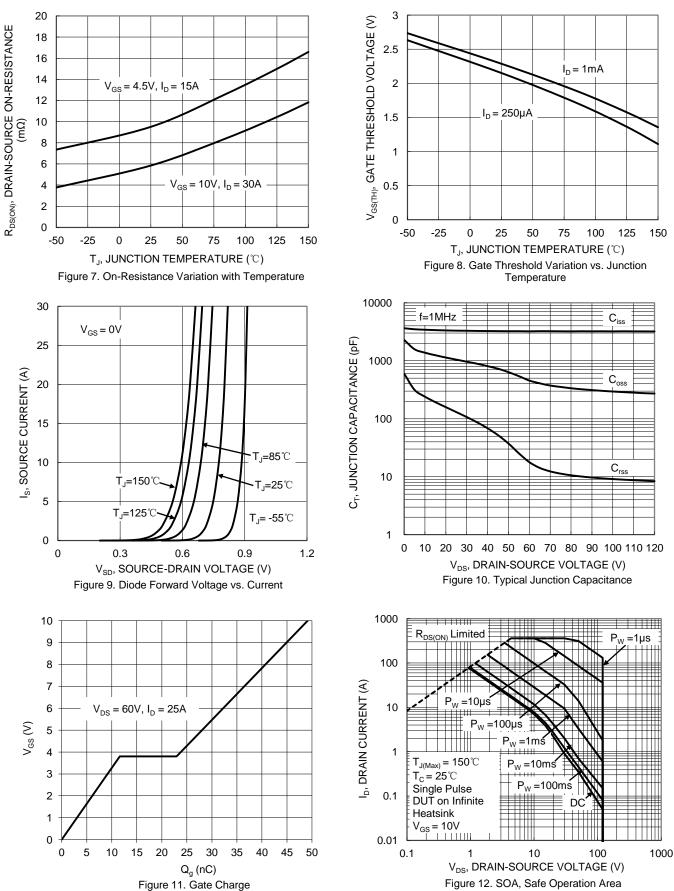
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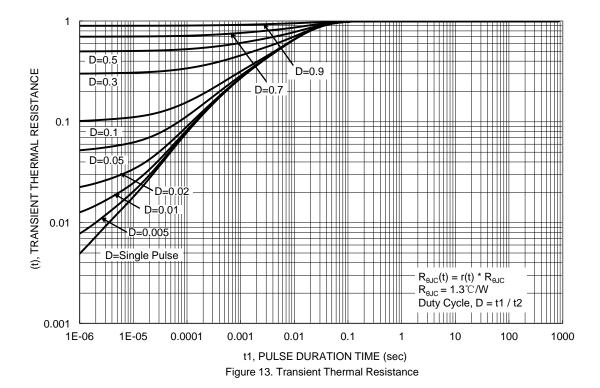


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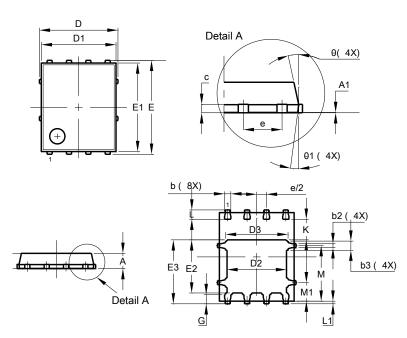






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

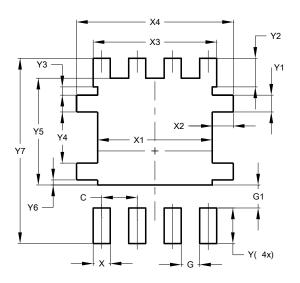


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PowerDI5060-8					
Dim	Min	Max	Тур		
Α	0.90	1.10	1.00		
A1	0.00	0.05	-		
b	0.33	0.51	0.41		
b2	0.200	0.350	0.273		
b3	0.40	0.80	0.60		
С	0.230	0.330	0.277		
D		5.15 BSC			
D1	4.70	5.10	4.90		
D2	3.70	4.10	3.90		
D3	3.90 4.30 4.10				
E	6.15 BSC				
E1	5.60	6.00	5.80		
E2	3.28	3.68 3.4			
E3	3.99	.99 4.39 4.19			
е	1.27 BSC				
G	0.51	0.71	0.61		
K	0.51	0.51 – –			
L	0.51	0.51 0.71 0.61			
L1	0.100	0.200 0.17			
М	3.235	4.035	3.635		
M1	1.00	1.40	1.21		
Θ	10°	12°	11°		
Θ1	6°	8°	7°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
С	1.270
G	0.660
G1	0.820
Х	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

PowerDI5060-8



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